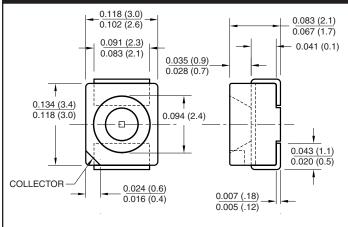


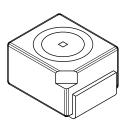
# QSB320 SURFACE MOUNT SILICON INFRARED PHOTOTRANSISTOR

### PACKAGE DIMENSIONS



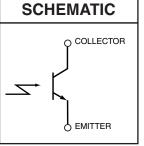
### NOTES:

- 1. Dimensions for all drawings are in inches (millimeters).
- 2. Tolerance of  $\pm$  .010 (.25) on all non nominal dimensions unless otherwise specified.



### **FEATURES**

- Surface Mount PLCC-2 Package
- Wide Reception Angle, 120°
- High Sensitivity
- Phototransistor Output
- Matched Emitter: QEB421



<b>ABSOLUTE MAXIMUM RATINGS</b> ( $T_A = 25^{\circ}C$ unless otherwise specified)							
Parameter	Symbol	Rating	Unit				
Operating Temperature	T <sub>OPR</sub>	-55 to +100	°C				
Storage Temperature	T <sub>STG</sub>	-55 to +100	°C				
Soldering Temperature (Flow) <sup>(2,3)</sup>	T <sub>SOL-F</sub>	260 for 10 sec	°C				
Collector Emitter Voltage	V <sub>CE</sub>	35	V				
Emitter Collector Voltage	V <sub>EC</sub>	5	V				
Collector Current	Ι <sub>C</sub>	15	mA				
Power Dissipation <sup>(1)</sup>	PD	165					

## NOTES

- 1. Derate power dissipation linearly 2.2 mW/°C above 25°C.
- 2. RMA flux is recommended.
- 3. Methanol or isopropyl alcohols are recommended as cleaning agents.
- 4.  $\lambda = 940$  nm.

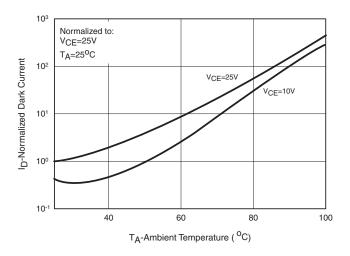
## ELECTRICAL / OPTICAL CHARACTERISTICS (T<sub>A</sub> =25°C)

PARAMETER	TEST CONDITIONS	SYMBOL	MIN	TYP	MAX	UNITS
Peak Sensitivity Wavelength		$\lambda_{PS}$	—	880	_	nm
Wavelength Sensitivity Range		$\lambda_{SR}$	400	—	1000	nm
Reception Angle		θ	_	120	_	Deg.
Collector Emitter Dark Current	$V_{CE} = 25 V, E_{e} = 0$	I <sub>D</sub>	_	_	200	nA
Collector Emitter Breakdown	$I_{\rm C} = 1  \mathrm{mA}$	$BV_{CEO}$	30	—		V
Emitter Collector Breakdown	I <sub>E</sub> = 100 μA	$BV_{ECO}$	5	_	_	V
On-State Collector Current	$E_e = 0.1 \text{ mW/cm}^{2(4)}, V_{CE} = 5 \text{ V}$	I <sub>C (ON)</sub>	16	_	_	μA
Saturation Voltage	$E_e = 0.5 \text{ mW/cm}^{2(4)}, \ I_C = 0.05 \text{ mA}$	V <sub>CE (SAT)</sub>	—	—	0.3	V
Rise Time	$V_{CC}$ = 5 V, $R_L$ = 100 $\Omega$	t <sub>r</sub>		8		μs
Fall Time	$I_{\rm C} = 1  \rm{mA}$	t <sub>f</sub>	—	8	—	μs



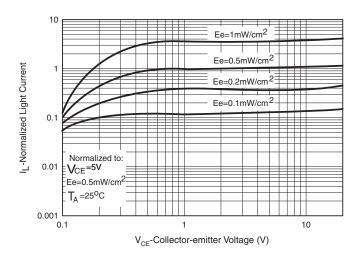
## **QSB320** SURFACE MOUNT SILICON INFRARED PHOTOTRANSISTOR

Fig.2 Dark Current Vs. Collector Emitter Voltage



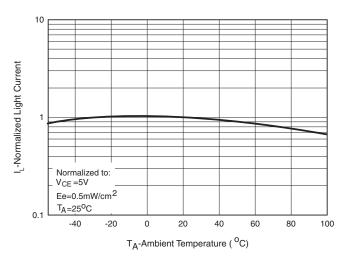
#### Fig.1 Dark Current Vs. Ambient Temperature

Fig.3 Light Current Vs. Collector to Emitter Voltage



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Fig4. Light Current Vs. Ambient Temperature





# QSB320 SURFACE MOUNT SILICON INFRARED PHOTOTRANSISTOR

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